

Serial No.: 10/098,524
Atty. Docket No.: P67503US0

IN THE SPECIFICATION:

On page 9, please amend the first full paragraph which begins on line 11, as follows:

--Once the surface of the second photoresist 105a is cured, the STI region (104b of Fig. 4C) ~~fo~~ of the semiconductor substrate 100 is etched more deeply by using the cured second photoresist 105a and the second insulating layer 102 as a mask, thereby forming a DTI region 106. The DTI region 106 has a depth of 7000~8000Å from the surface of the semiconductor substrate 100.--